

**ABSTRACT OF THE DISCLOSURE**

A nonvolatile semiconductor memory device includes a plurality of blocks each having a nonvolatile memory cell array, and a program  
5 potential generating circuit which supplies a program potential to the nonvolatile memory cell array, wherein the program potential generating circuit adjusts the program potential according to a first address signal selecting one of the blocks and  
10 a second address signal indicating a position of a write-accessed memory cell in the noted one of the blocks.